

$V_{RRM} = 2500 \text{ V}$

$I_F = 108 \text{ A}$

Fast-Diode Die

5SLX 12L2507



Die size: 12.4 x 12.4 mm

Doc. No. 5SYA1667-00 Dec 06

- Fast and soft reverse-recovery
- Low losses
- High SOA
- Passivation: SIPOS Nitride plus Polyimide

Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	max	Unit
Repetitive peak reverse voltage	V_{RRM}			2500	V
Continuous forward current	I_F			108	A
Repetitive peak forward current	I_{FRM}	Limited by T_{vjmax}		216	A
Junction temperature	T_{vj}		-40	125	°C

¹⁾ Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747 - 2

Diode characteristic values ²⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Continuous forward voltage	V_F	$I_F = 108 \text{ A}$	$T_{vj} = 25 \text{ °C}$	1.95		V
			$T_{vj} = 125 \text{ °C}$	1.95		V
Continuous reverse current	I_R	$V_R = 2500 \text{ V}$	$T_{vj} = 25 \text{ °C}$	2		μA
			$T_{vj} = 125 \text{ °C}$	1.5	7	mA
Peak reverse recovery current	I_{rr}	$I_F = 108 \text{ A},$ $V_R = 1250 \text{ V},$ $di/dt = 420 \text{ A}/\mu\text{s},$ $L_\sigma = 1200 \text{ nH},$ Inductive load, Switch: 2x 5SMX12L2511	$T_{vj} = 25 \text{ °C}$	85		A
			$T_{vj} = 125 \text{ °C}$	110		A
Recovered charge	Q_{rr}	$I_F = 108 \text{ A},$ $V_R = 1250 \text{ V},$ $di/dt = 420 \text{ A}/\mu\text{s},$ $L_\sigma = 1200 \text{ nH},$ Inductive load, Switch: 2x 5SMX12L2511	$T_{vj} = 25 \text{ °C}$	43		μC
			$T_{vj} = 125 \text{ °C}$	80		μC
Reverse recovery time	t_{rr}	$I_F = 108 \text{ A},$ $V_R = 1250 \text{ V},$ $di/dt = 420 \text{ A}/\mu\text{s},$ $L_\sigma = 1200 \text{ nH},$ Inductive load, Switch: 2x 5SMX12L2511	$T_{vj} = 25 \text{ °C}$	600		ns
			$T_{vj} = 125 \text{ °C}$	1020		ns
Reverse recovery energy	E_{rec}	$I_F = 108 \text{ A},$ $V_R = 1250 \text{ V},$ $di/dt = 420 \text{ A}/\mu\text{s},$ $L_\sigma = 1200 \text{ nH},$ Inductive load, Switch: 2x 5SMX12L2511	$T_{vj} = 25 \text{ °C}$	37		mJ
			$T_{vj} = 125 \text{ °C}$	70		mJ

²⁾ Characteristic values according to IEC 60747 - 2

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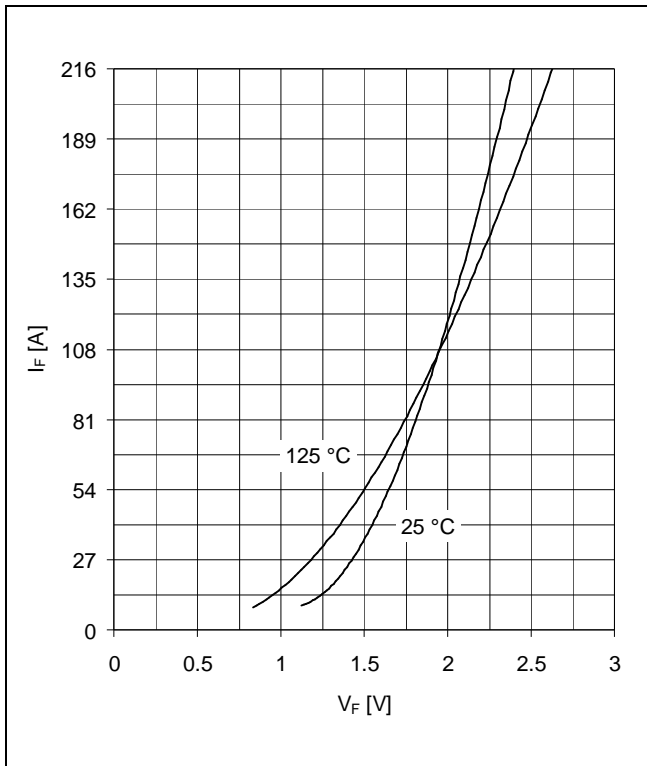


Fig. 1 Typical forward characteristics

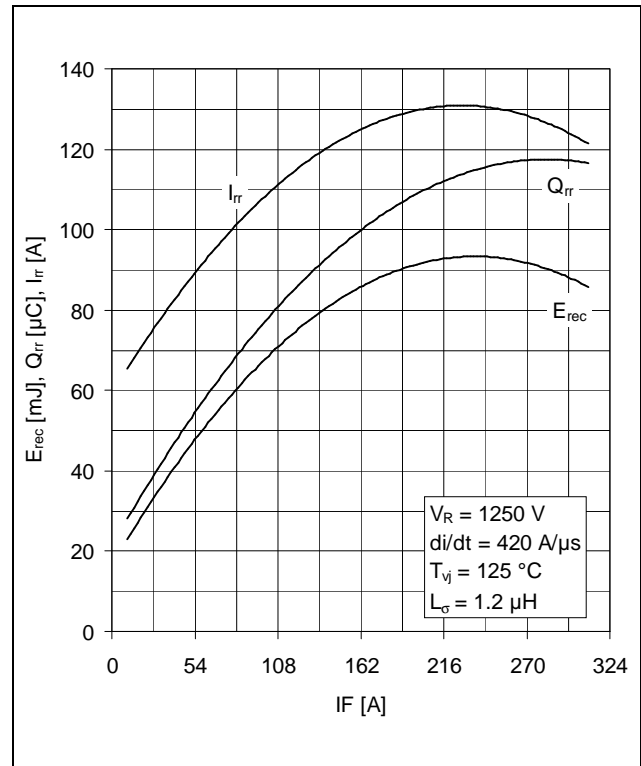


Fig. 2 Typical reverse recovery characteristics vs. forward current

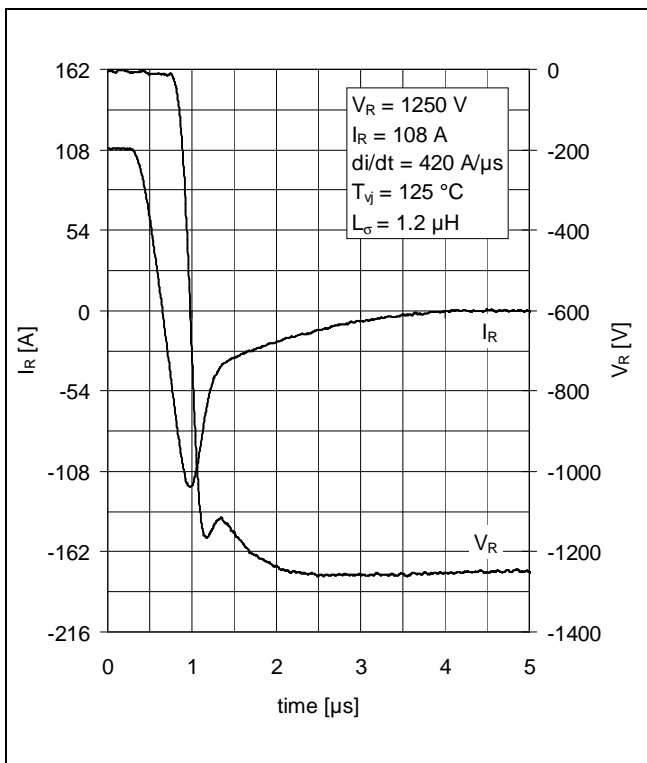


Fig. 3 Typical reverse recovery behaviour

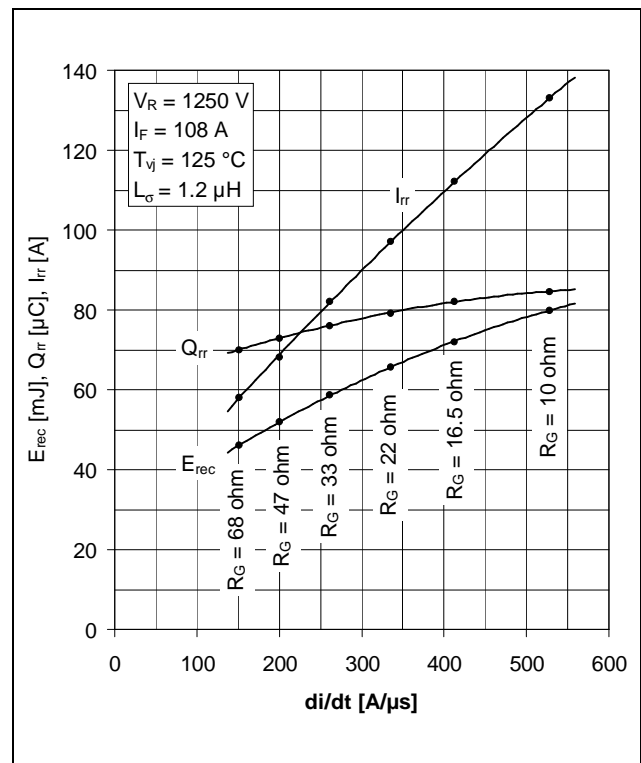


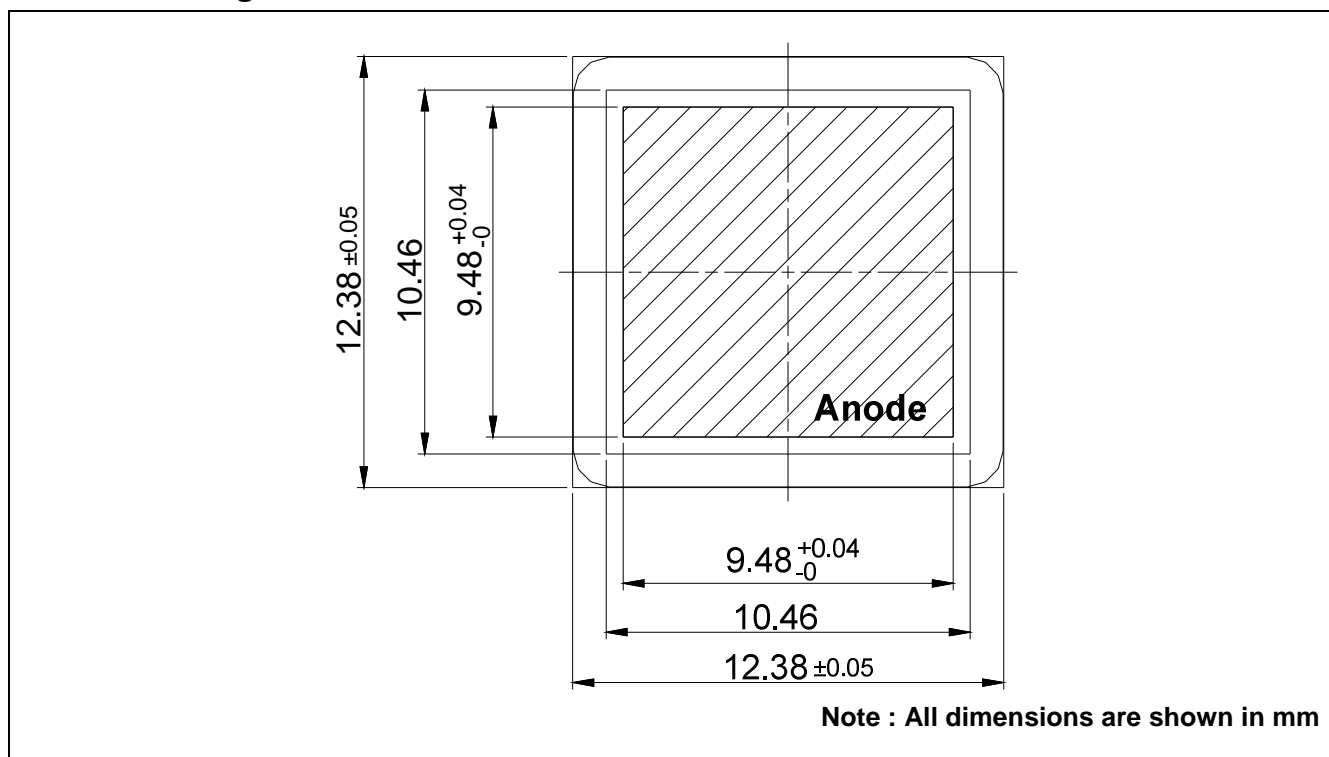
Fig. 4 Typical reverse recovery characteristics vs. di/dt

Mechanical properties

Parameter				Unit
Dimensions	Overall die	L x W	12.4 x 12.4	mm
	exposed front metal	L x W	9.48 x 9.48	mm
	thickness		310 ± 20	µm
Metallization ³⁾	front (A)	AlSi1 + TiNiAg	4 + 4	µm
	back (K)	AlSi1 + TiNiAg	1.8 + 1.2	µm

³⁾ For assembly instructions refer to: IGBT and Diode chips from ABB Switzerland Ltd, Semiconductors, Doc. No. 5SYA 2033.

Outline Drawing



This product has been designed and qualified for Industrial Level.

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